

Stephen J Pearton

List of Publications by Year in descending order

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2,146
papers

69,441
citations

1606

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2736

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2179
all docs

2179
docs citations

2179
times ranked

27825
citing authors

#	ARTICLE	IF	CITATIONS
1	A review of Ga ₂ O ₃ materials, processing, and devices. Applied Physics Reviews, 2018, 5, .	5.5	1,816
2	GaN: Processing, defects, and devices. Journal of Applied Physics, 1999, 86, 1-78.	1.1	1,657
3	Whispering gallery mode microdisk lasers. Applied Physics Letters, 1992, 60, 289-291.	1.5	1,335
4	Wide band gap ferromagnetic semiconductors and oxides. Journal of Applied Physics, 2003, 93, 1-13.	1.1	987
5	Hydrogen in crystalline semiconductors. Applied Physics A: Solids and Surfaces, 1987, 43, 153-195.	1.4	913
6	The Blue Laser Diode. , 2000, , .		774
7	ZnO: growth, doping & processing. Materials Today, 2004, 7, 34-40.	8.3	684
8	Recent advances in processing of ZnO. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 932.	1.6	619
9	Hydrogen in Crystalline Semiconductors. Springer Series in Materials Science, 1992, , .	0.4	552
10	ZnO nanowire growth and devices. Materials Science and Engineering Reports, 2004, 47, 1-47.	14.8	534
11	Hydrogen-selective sensing at room temperature with ZnO nanorods. Applied Physics Letters, 2005, 86, 243503.	1.5	524
12	Dilute magnetic semiconducting oxides. Semiconductor Science and Technology, 2004, 19, R59-R74.	1.0	509
13	Hydrogen interactions with defects in crystalline solids. Reviews of Modern Physics, 1992, 64, 559-617.	16.4	471
14	Optically detected carrier confinement to one and zero dimension in GaAs quantum well wires and boxes. Applied Physics Letters, 1986, 49, 1275-1277.	1.5	470
15	Single-electron capacitance spectroscopy of discrete quantum levels. Physical Review Letters, 1992, 68, 3088-3091.	2.9	441
16	Fabrication and performance of GaN electronic devices. Materials Science and Engineering Reports, 2000, 30, 55-212.	14.8	423
17	Perspective: Ga ₂ O ₃ for ultra-high power rectifiers and MOSFETS. Journal of Applied Physics, 2018, 124, .	1.1	416
18	Advances in wide bandgap materials for semiconductor spintronics. Materials Science and Engineering Reports, 2003, 40, 137-168.	14.8	409

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19	Ferromagnetism in Mn-implanted ZnO:Sn single crystals. Applied Physics Letters, 2003, 82, 239-241.	1.5	403
20	Origin of green luminescence in ZnO thin film grown by molecular-beam epitaxy. Journal of Applied Physics, 2005, 98, 073502.	1.1	373
21	Ion implantation into GaN. Materials Science and Engineering Reports, 2001, 33, 51-108.	14.8	370
22	Perspective "Opportunities and Future Directions for Ga ₂ O ₃ . ECS Journal of Solid State Science and Technology, 2017, 6, P356-P359.	0.9	352
23	Recent progress in processing and properties of ZnO. Superlattices and Microstructures, 2003, 34, 3-32.	1.4	343
24	Magnetic properties of n-GaMnN thin films. Applied Physics Letters, 2002, 80, 3964-3966.	1.5	328
25	Hydrogen Sensing Using Pd-Functionalized Multi-Layer Graphene Nanoribbon Networks. Advanced Materials, 2010, 22, 4877-4880.	11.1	313
26	Ion implantation for isolation of III-V semiconductors. Materials Science and Engineering Reports, 1990, 4, 313-363.	5.8	306
27	Ion implantation doping and isolation of GaN. Applied Physics Letters, 1995, 67, 1435-1437.	1.5	285
28	Magnetic and structural properties of Mn-implanted GaN. Applied Physics Letters, 2001, 78, 3475-3477.	1.5	268
29	Indication of ferromagnetism in molecular-beam-epitaxy-derived N-type GaMnN. Applied Physics Letters, 2001, 79, 1312-1314.	1.5	268
30	GaN-based diodes and transistors for chemical, gas, biological and pressure sensing. Journal of Physics Condensed Matter, 2004, 16, R961-R994.	0.7	263
31	Hydrogen sensing at room temperature with Pt-coated ZnO thin films and nanorods. Applied Physics Letters, 2005, 87, 222106.	1.5	262
32	Ferromagnetism in cobalt-implanted ZnO. Applied Physics Letters, 2003, 83, 5488-5490.	1.5	251
33	Recent advances in wide bandgap semiconductor biological and gas sensors. Progress in Materials Science, 2010, 55, 1-59.	16.0	247
34	Review "Ionizing Radiation Damage Effects on GaN Devices. ECS Journal of Solid State Science and Technology, 2016, 5, Q35-Q60.	0.9	243
35	Threshold characteristics of semiconductor microdisk lasers. Applied Physics Letters, 1993, 63, 1310-1312.	1.5	241
36	Depletion-mode ZnO nanowire field-effect transistor. Applied Physics Letters, 2004, 85, 2274-2276.	1.5	228

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37	Donor neutralization in GaAs(Si) by atomic hydrogen. Applied Physics Letters, 1985, 47, 108-110.	1.5	225
38	Effect of temperature on Ga ₂ O ₃ (Gd ₂ O ₃)/GaN metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 1998, 73, 3893-3895.	1.5	217
39	Ultrahigh doping of GaAs by carbon during metalorganic molecular beam epitaxy. Applied Physics Letters, 1989, 55, 1750-1752.	1.5	215
40	Unconventional Carrier-Mediated Ferromagnetism above Room Temperature in Ion-Implanted (Ga, _{0.01} Er) _{0.99} As. Applied Physics Letters, 2010, 96, 122104.	2.9	214
41	GaN Electronics. Advanced Materials, 2000, 12, 1571-1580.	11.1	208
42	Donor-hydrogen complexes in passivated silicon. Physical Review B, 1988, 37, 2770-2773.	1.1	206
43	p-type behavior in phosphorus-doped (Zn,Mg)O device structures. Applied Physics Letters, 2004, 84, 3474-3476.	1.5	201
44	1.54- μ m photoluminescence from Er-implanted GaN and AlN. Applied Physics Letters, 1994, 65, 992-994.	1.5	197
45	Inductively coupled plasma etching of GaN. Applied Physics Letters, 1996, 69, 1119-1121.	1.5	197
46	Hydrogen incorporation and diffusivity in plasma-exposed bulk ZnO. Applied Physics Letters, 2003, 82, 385-387.	1.5	196
47	A survey of ohmic contacts to III-V compound semiconductors. Thin Solid Films, 1997, 308-309, 599-606.	0.8	192
48	Electrical effects of plasma damage in p-GaN. Applied Physics Letters, 1999, 75, 2569-2571.	1.5	188
49	Ca and O ion implantation doping of GaN. Applied Physics Letters, 1996, 68, 1945-1947.	1.5	184
50	Electrical characteristics of Au and Ag Schottky contacts on n-ZnO. Applied Physics Letters, 2003, 83, 1575-1577.	1.5	180
51	Kinetics of implantation enhanced interdiffusion of Ga and Al at GaAs-GaxAl _{1-x} As interfaces. Applied Physics Letters, 1986, 49, 223-225.	1.5	178
52	Directional light coupling from microdisk lasers. Applied Physics Letters, 1993, 62, 561-563.	1.5	174
53	Radiation effects in GaN materials and devices. Journal of Materials Chemistry C, 2013, 1, 877-887.	2.7	171
54	Hydrogenation of shallow donor levels in GaAs. Journal of Applied Physics, 1986, 59, 2821-2827.	1.1	170

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55	A Review of Dry Etching of GaN and Related Materials. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 1.	1.0	170
56	Review of radiation damage in GaN-based materials and devices. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	0.9	170
57	2300V Reverse Breakdown Voltage Ga ₂ O ₃ Schottky Rectifiers. ECS Journal of Solid State Science and Technology, 2018, 7, Q92-Q96.	0.9	169
58	Ion-implanted GaN junction field effect transistor. Applied Physics Letters, 1996, 68, 2273-2275.	1.5	167
59	Effects of high-dose Mn implantation into ZnO grown on sapphire. Applied Physics Letters, 2004, 84, 2292-2294.	1.5	167
60	Influence of MgO and Sc ₂ O ₃ passivation on AlGaIn/GaN high-electron-mobility transistors. Applied Physics Letters, 2002, 80, 1661-1663.	1.5	165
61	Structure and magnetism of cobalt-doped ZnO thin films. New Journal of Physics, 2008, 10, 065002.	1.2	164
62	High Breakdown Voltage (~ 201) η -Ga ₂ O ₃ Schottky Rectifiers. IEEE Electron Device Letters, 2017, 38, 906-909.	2.2	159
63	MgZnO δ -AlGaIn heterostructure light-emitting diodes. Applied Physics Letters, 2004, 85, 4272.	1.5	157
64	Hydrogen local modes and shallow donors in ZnO. Physical Review B, 2005, 72, .	1.1	154
65	Radiation damage effects in Ga ₂ O ₃ materials and devices. Journal of Materials Chemistry C, 2019, 7, 10-24.	2.7	154
66	Wet chemical etching of AlN. Applied Physics Letters, 1995, 67, 1119-1121.	1.5	151
67	High reverse breakdown voltage Schottky rectifiers without edge termination on Ga ₂ O ₃ . Applied Physics Letters, 2017, 110, .	1.5	149
68	ZnO spintronics and nanowire devices. Journal of Electronic Materials, 2006, 35, 862-868.	1.0	148
69	Vibrational characteristics of acceptor-hydrogen complexes in silicon. Applied Physics Letters, 1987, 50, 1086-1088.	1.5	146
70	Electrical transport properties of single ZnO nanorods. Applied Physics Letters, 2004, 85, 2002-2004.	1.5	146
71	Carbon nanotube films for room temperature hydrogen sensing. Nanotechnology, 2005, 16, 2218-2221.	1.3	143
72	Hidden hydrogen in as-grown ZnO. Applied Physics Letters, 2004, 85, 5601-5603.	1.5	141

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73	Transport properties of phosphorus-doped ZnO thin films. Applied Physics Letters, 2003, 83, 1128-1130.	1.5	140
74	Room temperature operation of microdisc lasers with submilliamp threshold current. Electronics Letters, 1992, 28, 1010-1012.	0.5	139
75	ZnO Doped With Transition Metal Ions. IEEE Transactions on Electron Devices, 2007, 54, 1040-1048.	1.6	137
76	Depth and thermal stability of dry etch damage in GaN Schottky diodes. Applied Physics Letters, 1999, 75, 232-234.	1.5	136
77	pH measurements with single ZnO nanorods integrated with a microchannel. Applied Physics Letters, 2005, 86, 112105.	1.5	135
78	Electroluminescence from ZnO nanowire/polymer composite p-n junction. Applied Physics Letters, 2006, 88, 173503.	1.5	135
79	Low bias electron cyclotron resonance plasma etching of GaN, AlN, and InN. Applied Physics Letters, 1994, 64, 2294-2296.	1.5	134
80	Room temperature deposited indium zinc oxide thin film transistors. Applied Physics Letters, 2007, 90, 232103.	1.5	132
81	AlGaIn/GaN metal-oxide semiconductor high electron mobility transistors using Sc ₂ O ₃ as the gate oxide and surface passivation. Applied Physics Letters, 2003, 82, 2530-2532.	1.5	130
82	Flexible graphene-based chemical sensors on paper substrates. Physical Chemistry Chemical Physics, 2013, 15, 1798-1801.	1.3	130
83	Pt-ZnO nanowire Schottky diodes. Applied Physics Letters, 2004, 85, 3107-3109.	1.5	129
84	Contacts to ZnO. Journal of Crystal Growth, 2006, 287, 149-156.	0.7	125
85	CCl ₄ doping of GaN grown by metalorganic molecular beam epitaxy. Applied Physics Letters, 1995, 66, 1969-1971.	1.5	122
86	Effects of ambient atmosphere on the transfer characteristics and gate-bias stress stability of amorphous indium-gallium-zinc oxide thin-film transistors. Applied Physics Letters, 2010, 96, .	1.5	121
87	Ion implantation damage and annealing in InAs, GaSb, and GaP. Journal of Applied Physics, 1988, 64, 629-636.	1.1	119
88	Carbon doping of III-V compounds grown by MOMBE. Journal of Crystal Growth, 1990, 105, 375-382.	0.7	118
89	Damage to epitaxial GaN layers by silicon implantation. Applied Physics Letters, 1996, 69, 2364-2366.	1.5	118
90	Electrical detection of immobilized proteins with ungated AlGaIn-GaN high-electron-mobility Transistors. Applied Physics Letters, 2005, 87, 023508.	1.5	118

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91	Wide bandgap GaN-based semiconductors for spintronics. <i>Journal of Physics Condensed Matter</i> , 2004, 16, R209-R245.	0.7	117
92	Enzymatic glucose detection using ZnO nanorods on the gate region of AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , 2007, 91, .	1.5	117
93	Oxygen and zinc vacancies in as-grown ZnO single crystals. <i>Journal Physics D: Applied Physics</i> , 2009, 42, 175411.	1.3	117
94	Oxygen sensors made by monolayer graphene under room temperature. <i>Applied Physics Letters</i> , 2011, 99, 243502.	1.5	116
95	High temperature electron cyclotron resonance etching of GaN, InN, and AlN. <i>Applied Physics Letters</i> , 1995, 66, 1761-1763.	1.5	115
96	Electrical detection of biomaterials using AlGaIn/GaN high electron mobility transistors. <i>Journal of Applied Physics</i> , 2008, 104, .	1.1	114
97	Hydrogen passivation of gold-related deep levels in silicon. <i>Physical Review B</i> , 1982, 26, 7105-7108.	1.1	113
98	Thermal stability of W ohmic contacts to AlGaIn/GaN. <i>Journal of Applied Physics</i> , 1996, 80, 278-281.	1.1	113
99	Pressure-induced changes in the conductivity of AlGaIn/GaN high-electron mobility-transistor membranes. <i>Applied Physics Letters</i> , 2004, 85, 2962-2964.	1.5	111
100	Quasi-two-dimensional β -gallium oxide solar-blind photodetectors with ultrahigh responsivity. <i>Journal of Materials Chemistry C</i> , 2016, 4, 9245-9250.	2.7	111
101	High-density plasma etching of compound semiconductors. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1997, 15, 633-637.	0.9	109
102	Vibrational spectroscopy of acceptor-hydrogen complexes in silicon: Evidence for low-frequency excitations. <i>Physical Review B</i> , 1988, 37, 8313-8318.	1.1	108
103	Advances in ZnO-based materials for light emitting diodes. <i>Current Opinion in Chemical Engineering</i> , 2014, 3, 51-55.	3.8	108
104	Electrical and structural analysis of high-dose Si implantation in GaN. <i>Applied Physics Letters</i> , 1997, 70, 2729-2731.	1.5	107
105	UV photoresponse of single ZnO nanowires. <i>Applied Physics A: Materials Science and Processing</i> , 2005, 80, 497-499.	1.1	107
106	High performance indium gallium zinc oxide thin film transistors fabricated on polyethylene terephthalate substrates. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	107
107	Passivation of deep level defects in molecular beam epitaxial GaAs by hydrogen plasma exposure. <i>Applied Physics Letters</i> , 1986, 49, 1098-1100.	1.5	106
108	dc and rf performance of proton-irradiated AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , 2001, 79, 2196-2198.	1.5	106

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109	Hydrogen Motion in Defect Complexes: Reorientation Kinetics of the B-H Complex in Silicon. <i>Physical Review Letters</i> , 1988, 61, 2786-2789.	2.9	104
110	MgO/p-GaN enhancement mode metal-oxide semiconductor field-effect transistors. <i>Applied Physics Letters</i> , 2004, 84, 2919-2921.	1.5	104
111	Functionalizing Zn- and O-terminated ZnO with thiols. <i>Journal of Applied Physics</i> , 2007, 101, 104514.	1.1	104
112	Ferromagnetism in Mn- and Co-implanted ZnO nanorods. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 1476.	1.6	103
113	Growth of high quality AlGaAs by metalorganic molecular beam epitaxy using trimethylamine alane. <i>Applied Physics Letters</i> , 1990, 56, 2654-2656.	1.5	102
114	Plasma etching of III-V semiconductors in CH ₄ /H ₂ /Ar electron cyclotron resonance discharges. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1990, 8, 596.	1.6	102
115	Magnetic and structural properties of Co, Cr, V ion-implanted GaN. <i>Journal of Applied Physics</i> , 2003, 93, 4512-4516.	1.1	102
116	Dry and wet etching characteristics of InN, AlN, and GaN deposited by electron cyclotron resonance metalorganic molecular beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1993, 11, 1772-1775.	0.9	101
117	Hydrogen and ozone gas sensing using multiple ZnO nanorods. <i>Applied Physics A: Materials Science and Processing</i> , 2005, 80, 1029-1032.	1.1	101
118	Implant-induced high-resistivity regions in InP and InGaAs. <i>Journal of Applied Physics</i> , 1989, 66, 656-662.	1.1	100
119	Single Wall Carbon Nanotubes for p-Type Ohmic Contacts to GaN Light-Emitting Diodes. <i>Nano Letters</i> , 2004, 4, 911-914.	4.5	100
120	Influence of High-Energy Proton Irradiation on ² Ga ₂ O ₃ Nanobelt Field-Effect Transistors. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 40471-40476.	4.0	100
121	Lattice Location of Deuterium Interacting with the Boron Acceptor in Silicon. <i>Physical Review Letters</i> , 1988, 60, 321-324.	2.9	99
122	Dry Etching of Electronic Oxides, Polymers, and Semiconductors. <i>Plasma Processes and Polymers</i> , 2005, 2, 16-37.	1.6	98
123	Hydrogen detection using platinum coated graphene grown on SiC. <i>Sensors and Actuators B: Chemical</i> , 2011, 157, 500-503.	4.0	98
124	Point defect induced degradation of electrical properties of Ga ₂ O ₃ by 10 ¹⁶ MeV proton damage. <i>Applied Physics Letters</i> , 2018, 112, .	1.5	98
125	Effect of external strain on the conductivity of AlGaIn/GaN high-electron-mobility transistors. <i>Applied Physics Letters</i> , 2003, 83, 4845-4847.	1.5	97
126	Fabrication of p-channel thin-film transistors using CuO active layers deposited at low temperature. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	97

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127	Gd ₂ O ₃ /GaN metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2000, 77, 3230-3232.	1.5	96
128	Thermal stability of ion-implanted hydrogen in ZnO. Applied Physics Letters, 2002, 81, 3996-3998.	1.5	96
129	Passivation of Si donors and DX centers in AlGaAs by hydrogen plasma exposure. Applied Physics Letters, 1987, 50, 921-923.	1.5	95
130	GaN electronics for high power, high temperature applications. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 82, 227-231.	1.7	95
131	Characteristics of MgO/GaN gate-controlled metal-oxide semiconductor diodes. Applied Physics Letters, 2002, 80, 4555-4557.	1.5	95
132	Plasma and wet chemical etching of In _{0.5} Ga _{0.5} P. Journal of Electronic Materials, 1992, 21, 441-445.	1.0	94
133	Prostate specific antigen detection using AlGaAs-GaN high electron mobility transistors. Applied Physics Letters, 2007, 91, .	1.5	94
134	High-Performance Indium Gallium Zinc Oxide Transparent Thin-Film Transistors Fabricated by Radio-Frequency Sputtering. Journal of the Electrochemical Society, 2008, 155, H383.	1.3	94
135	Wide Bandgap Semiconductor One-Dimensional Nanostructures for Applications in Nanoelectronics and Nanosensors. Nanomaterials and Nanotechnology, 2013, 3, 1.	1.2	94
136	Lateral Al _x Ga _{1-x} N power rectifiers with 9.7 kV reverse breakdown voltage. Applied Physics Letters, 2001, 78, 823-825.	1.5	93
137	Effect of front and back gates on In^{2+} -Ga ₂ O ₃ nano-belt field-effect transistors. Applied Physics Letters, 2016, 109, .	1.5	93
138	ION IMPLANTATION IN III-V SEMICONDUCTOR TECHNOLOGY. International Journal of Modern Physics B, 1993, 07, 4687-4761.	1.0	92
139	Ferromagnetism in Co- and Mn-doped ZnO. Solid-State Electronics, 2003, 47, 2231-2235.	0.8	92
140	Room temperature hydrogen detection using Pd-coated GaN nanowires. Applied Physics Letters, 2008, 93, .	1.5	91
141	Room temperature operation of submicrometre radius disk laser. Electronics Letters, 1993, 29, 1666.	0.5	90
142	Dry etch damage in InN, InGaN, and InAlN. Applied Physics Letters, 1995, 67, 2329-2331.	1.5	90
143	Electrical detection of deoxyribonucleic acid hybridization with AlGaAs-GaN high electron mobility transistors. Applied Physics Letters, 2006, 89, 122102.	1.5	90
144	Ferromagnetism in Transition-Metal Doped ZnO. Journal of Electronic Materials, 2007, 36, 462-471.	1.0	90

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145	AlGaIn/GaN-based metal-oxide-semiconductor diode-based hydrogen gas sensor. Applied Physics Letters, 2004, 84, 1123-1125.	1.5	89
146	Sputtered AlN encapsulant for high-temperature annealing of GaN. Applied Physics Letters, 1996, 69, 538-540.	1.5	88
147	Breakdown voltage and reverse recovery characteristics of free-standing GaN Schottky rectifiers. IEEE Transactions on Electron Devices, 2002, 49, 32-36.	1.6	88
148	High mobility InGaZnO4 thin-film transistors on paper. Applied Physics Letters, 2009, 94, .	1.5	87
149	Advances in Hydrogen, Carbon Dioxide, and Hydrocarbon Gas Sensor Technology Using GaN and ZnO-Based Devices. Sensors, 2009, 9, 4669-4694.	2.1	86
150	Structure of acceptor-hydrogen and donor-hydrogen complexes in silicon from uniaxial stress studies. Physical Review B, 1988, 38, 9643-9648.	1.1	85
151	Evidence for the existence of a negatively charged hydrogen species in plasma-treated n-type Si. Applied Physics Letters, 1990, 56, 949-951.	1.5	85
152	GaAs/AlGaAs microdisk lasers. Applied Physics Letters, 1994, 64, 1911-1913.	1.5	85
153	Effects of interfacial oxides on Schottky barrier contacts to n- and p-type GaN. Applied Physics Letters, 1999, 75, 4130-4132.	1.5	85
154	Indication of hysteresis in AlMnN. Applied Physics Letters, 2003, 83, 1758-1760.	1.5	85
155	Phosphorus doped ZnO light emitting diodes fabricated via pulsed laser deposition. Applied Physics Letters, 2008, 92, .	1.5	85
156	Hydrogen passivation of acceptors in n-type GaN. Journal of Applied Physics, 1989, 66, 1993-1996.	1.1	84
157	Improved performance of quantum well infrared photodetectors using random scattering optical coupling. Applied Physics Letters, 1994, 64, 960-962.	1.5	84
158	Zn _{0.9} Mg _{0.1} O/ZnO p-n junctions grown by pulsed-laser deposition. Applied Physics Letters, 2004, 85, 1169-1171.	1.5	84
159	Stability of carbon and beryllium-doped base GaAs/AlGaAs heterojunction bipolar transistors. Applied Physics Letters, 1991, 59, 3613-3615.	1.5	83
160	Growth and fabrication of GaN/AlGaIn heterojunction bipolar transistor. Applied Physics Letters, 1999, 74, 2702-2704.	1.5	83
161	Temperature-dependent characteristics of Pt Schottky contacts on n-type ZnO. Applied Physics Letters, 2004, 84, 2835-2837.	1.5	83
162	Structure and vibrational properties of the dominant O-H center in β -Ga ₂ O ₃ . Applied Physics Letters, 2018, 112, .	1.5	83

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163	Bulk acceptor compensation produced in p-type silicon at near ambient temperatures by a H ₂ O plasma. Applied Physics Letters, 1984, 44, 606-608.	1.5	82
164	Thermal stability of implanted dopants in GaN. Applied Physics Letters, 1995, 66, 2238-2240.	1.5	82
165	Inductively coupled plasma-induced etch damage of GaN p-n junctions. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 1139-1143.	0.9	82
166	Gadolinium Oxide and Scandium Oxide: Gate Dielectrics for GaN MOSFETs. Physica Status Solidi A, 2001, 188, 239-242.	1.7	82
167	Hydrogen sensing with Pt-functionalized GaN nanowires. Sensors and Actuators B: Chemical, 2009, 140, 196-199.	4.0	82
168	Patterning of AlN, InN, and GaN in KOH-based solutions. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 836-839.	0.9	81
169	Deep level, quenched-in defects in silicon doped with gold, silver, iron, copper or nickel. Journal of Physics C: Solid State Physics, 1983, 16, 1665-1673.	1.5	80
170	Room-temperature lasing action in In _{0.51} Ga _{0.49} P/In _{0.2} Ga _{0.8} As microcylinder laser diodes. Applied Physics Letters, 1993, 62, 2021-2023.	1.5	80
171	Synthesis and microstructure of vertically aligned ZnO nanowires grown by high-pressure-assisted pulsed-laser deposition. Journal of Materials Science, 2008, 43, 6925-6932.	1.7	80
172	Hydrogen injection and neutralization of boron acceptors in silicon boiled in water. Applied Physics Letters, 1986, 48, 590-592.	1.5	79
173	The electrical properties of deep copper- and nickel-related centers in silicon. Journal of Applied Physics, 1983, 54, 1375-1379.	1.1	78
174	Hydrogenation of GaN, AlN, and InN. Applied Physics Letters, 1994, 64, 2724-2726.	1.5	78
175	Proton implantation effects on electrical and recombination properties of undoped ZnO. Journal of Applied Physics, 2003, 94, 2895-2900.	1.1	78
176	Electrical and structural changes in the near surface of reactively ion etched InP. Applied Physics Letters, 1989, 55, 1633-1635.	1.5	77
177	High quality Al _x Ga _{1-x} As grown by organometallic vapor phase epitaxy using trimethylamine alane as the aluminum precursor. Applied Physics Letters, 1991, 58, 77-79.	1.5	77
178	High voltage GaN Schottky rectifiers. IEEE Transactions on Electron Devices, 2000, 47, 692-696.	1.6	77
179	Detection of hydrogen at room temperature with catalyst-coated multiple ZnO nanorods. Applied Physics A: Materials Science and Processing, 2005, 81, 1117-1119.	1.1	77
180	Optical and magnetic properties of Eu-doped GaN. Applied Physics Letters, 2006, 89, 1321-1323.	1.5	77

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181	Electrical properties of bulk semi-insulating \hat{I}^2 -Ga ₂ O ₃ (Fe). Applied Physics Letters, 2018, 113, .	1.5	77
182	Influence of ⁶⁰ Co \hat{I}^3 -rays on dc performance of AlGa _N /Ga _N high electron mobility transistors. Applied Physics Letters, 2002, 80, 604-606.	1.5	76
183	Temperature-Dependent Characteristics of Ni/Au and Pt/Au Schottky Diodes on \hat{I}^2 -Ga ₂ O ₃ . ECS Journal of Solid State Science and Technology, 2017, 6, P68-P72.	0.9	76
184	Ion implantation in GaAs. Nuclear Instruments & Methods in Physics Research B, 1987, 19-20, 369-380.	0.6	75
185	Hydrogen in carbon-doped GaAs grown by metalorganic molecular beam epitaxy. Applied Physics Letters, 1990, 57, 2561-2563.	1.5	75
186	Annealing of ion implanted gallium nitride. Applied Physics Letters, 1998, 72, 1190-1192.	1.5	75
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188	Ar-ion milling characteristics of III-nitrides. Journal of Applied Physics, 1994, 76, 1210-1215.	1.1	74
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